



# Silicon Photonics Photo-Detector Announcement

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**FORUM**

# Agenda

- Intel's Silicon Photonics Research
- 40G Modulator Recap
- **40G Photodetector Announcement**
- Vision of Future Terascale Platforms
- Summary

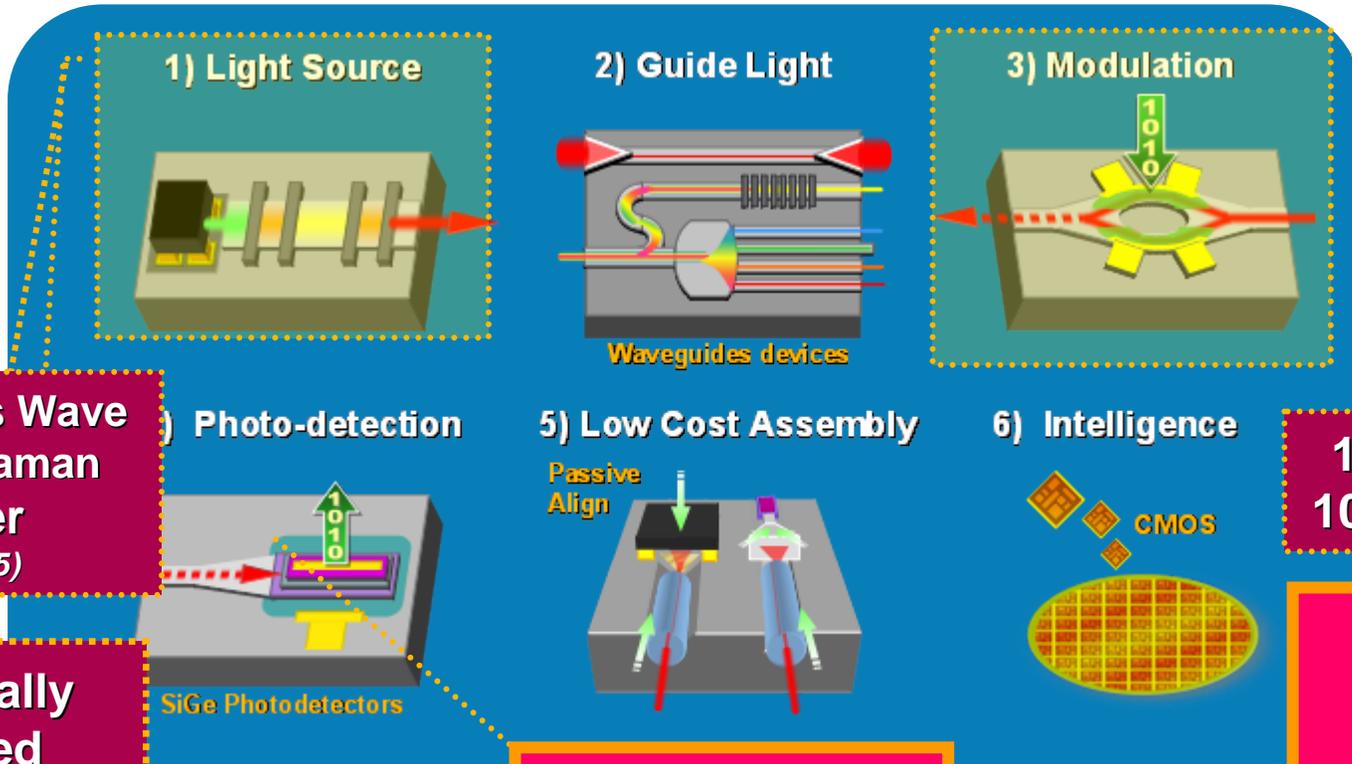
**Photonics: The technology of emission, transmission, control and detection of light (photons) aka fiber-optics & opto-electronics**

**Today: Most photonic devices made with exotic materials, expensive processing, complex packaging**

**Silicon Photonics Vision: Research effort to develop photonic devices using silicon as base material and do this using standard, high volume silicon manufacturing techniques in existing fabs**

**Benefit: Bring volume economics to optical communications**

# Intel's Silicon Photonics Research



**Continuous Wave Silicon Raman Laser**  
(Feb '05)

**Electrically Pumped Hybrid Silicon laser**  
(September 2006)

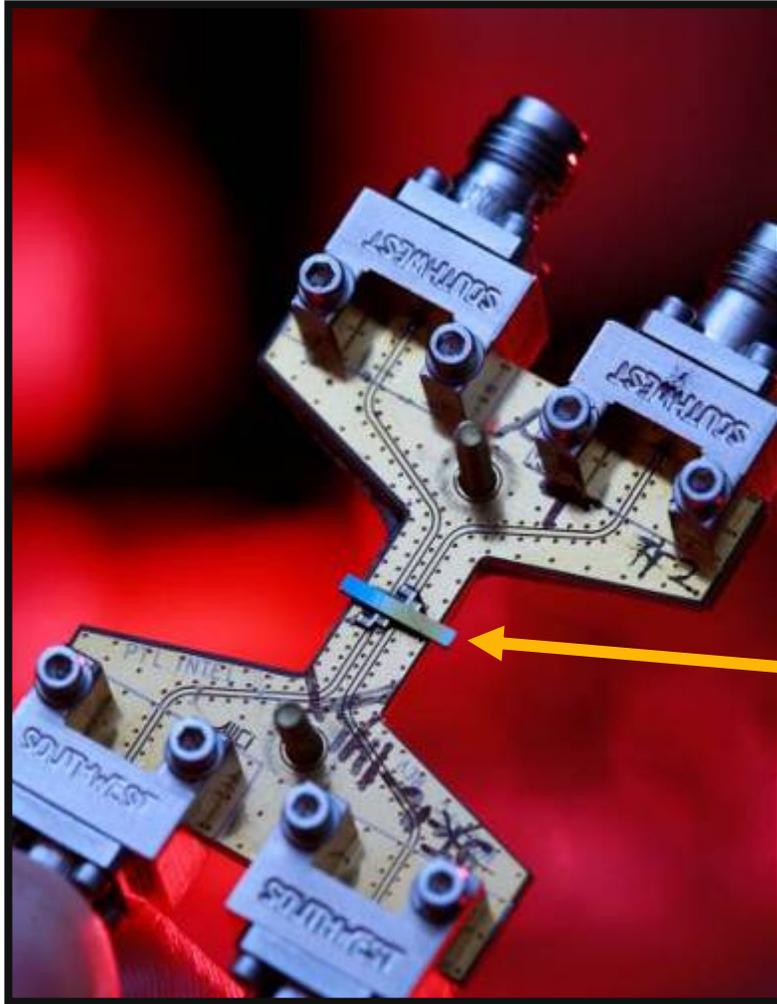
**1GHz (Feb '04)**  
**10 Gb/s (Apr '05)**

**40 Gb/s (Jul '07)**

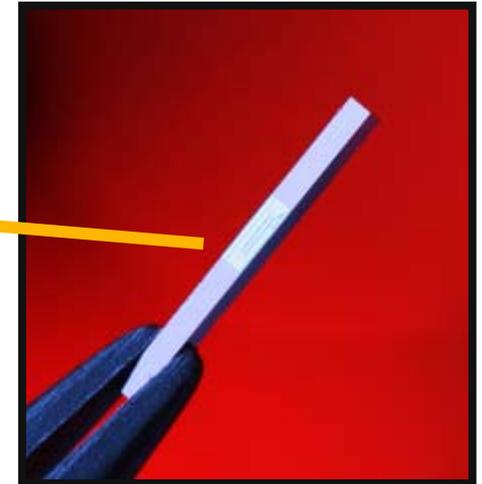
**40 Gb/s TODAY**

**Achieved 40 Gb/s for most devices**  
**Next: Focus on integration**

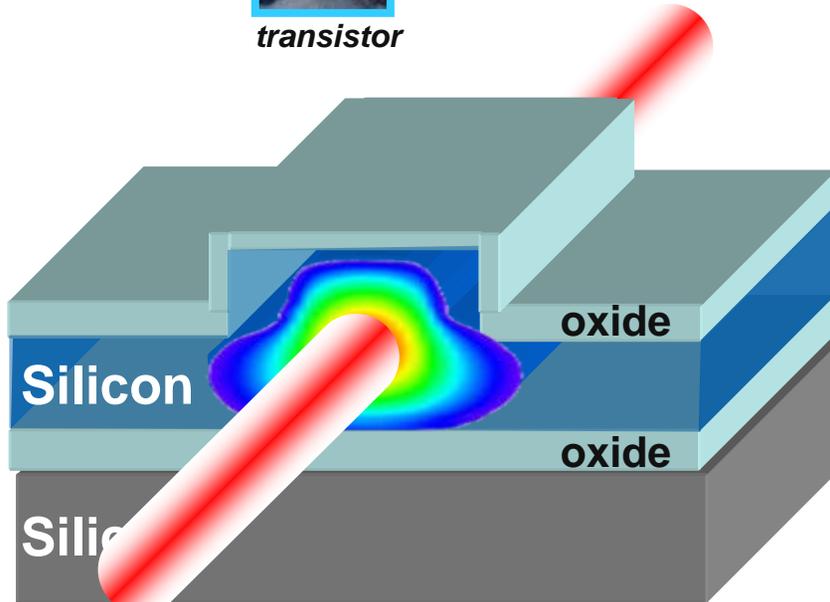
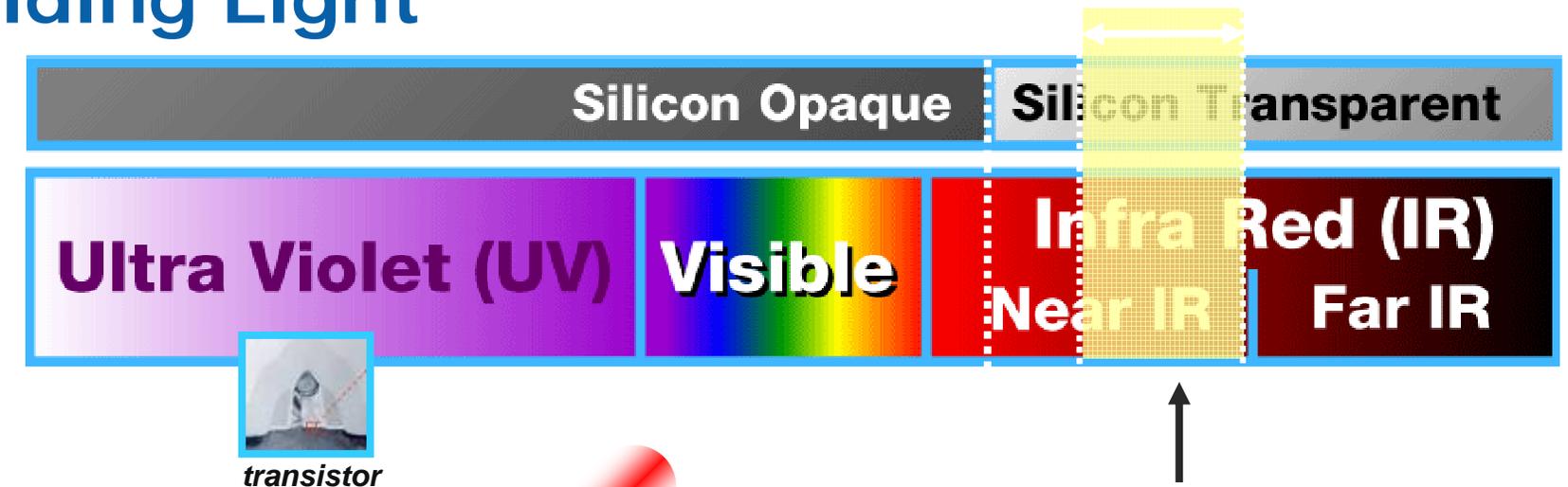
# 40Gb/s Silicon Laser Modulator



- Encodes data on a light beam at 40Gbps
- Fastest Si modulator
  - on par with fastest modulators available commercially



# Guiding Light



Ex: Rib waveguide

Silicon is Transparent to infra Red light ( $\lambda > 1.1\mu\text{m}$ )

Can guide light in Silicon

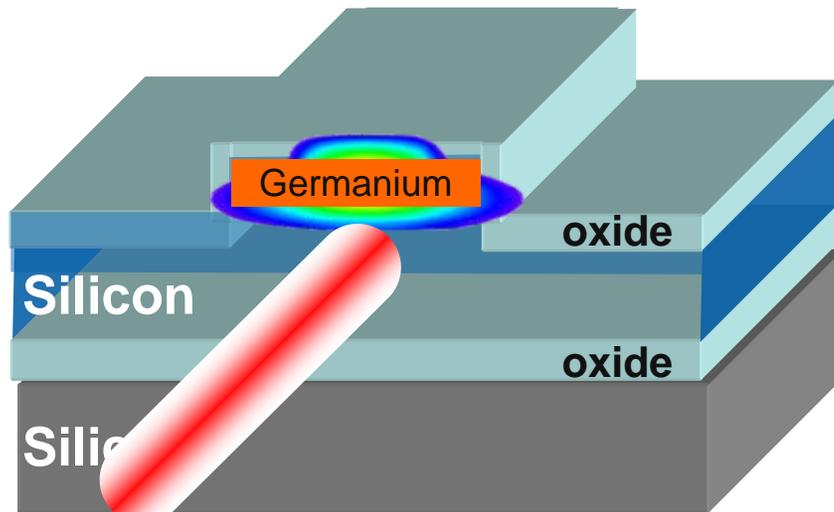
**But does not absorb/detect**

# How do we absorb light: Use Germanium

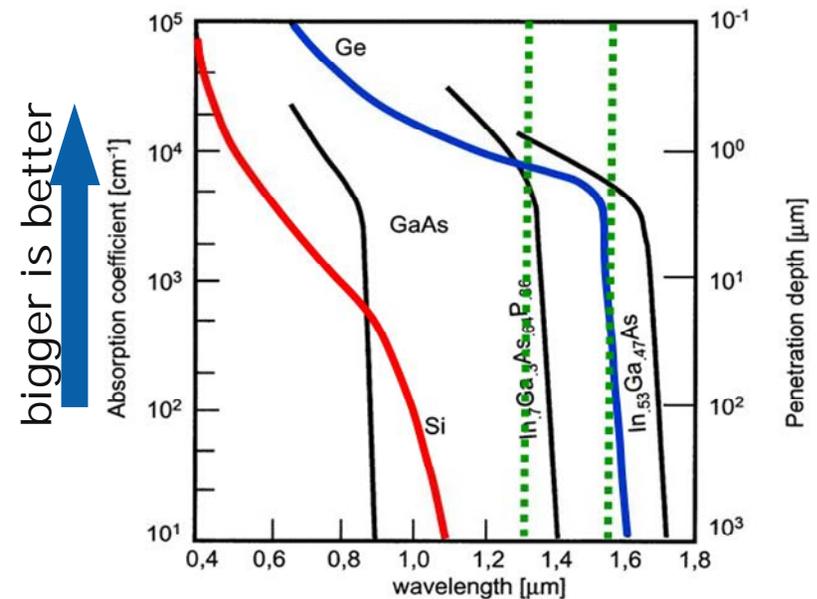
Bandgap engineering... i.e. add another material

*Ge is the most promising candidate:*

- High absorption for wavelengths of interest
- CMOS compatible

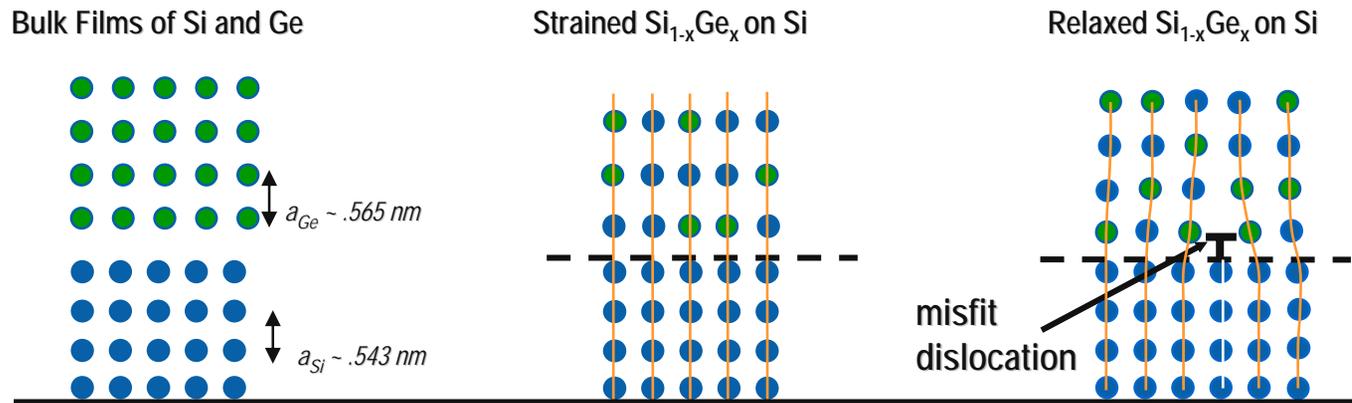


Ex: Rib waveguide



# Challenge: Strain

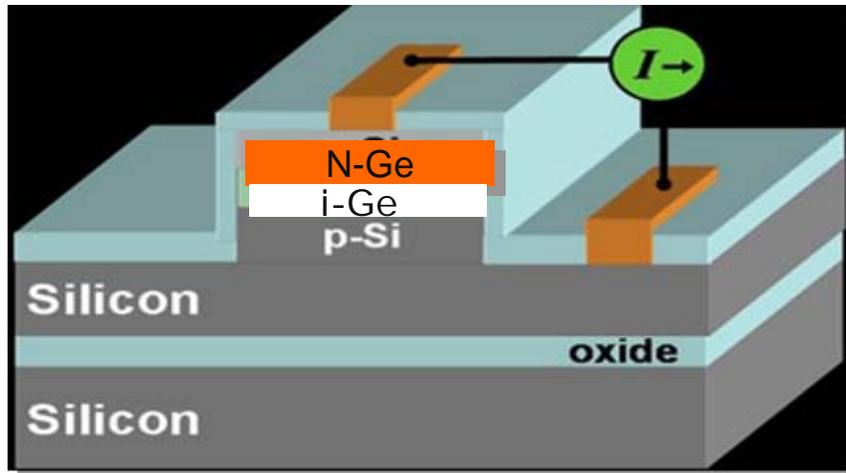
- Crystal structure of germanium is **4% larger** than silicon.
- This introduces strain when Ge is grown on Si.
- Result crystal lattice dislocations → excess noise



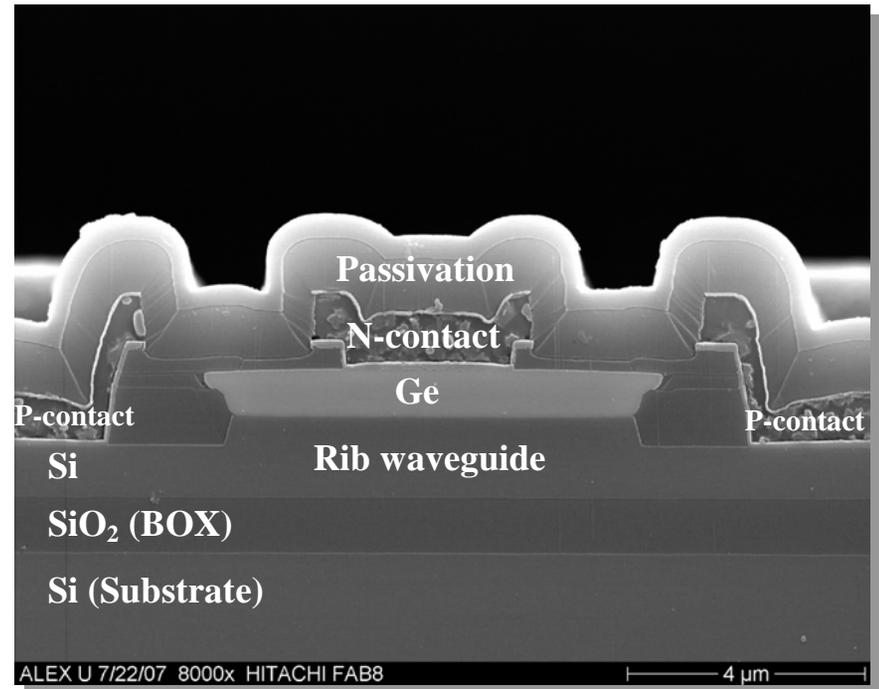
Misfit dislocations typically create threading dislocations which degrade device performance - dark current ( $I_{dk}$ ) goes up.

By optimizing the thermal growth process parameters we can minimize defects impact.

# Photodetector Design



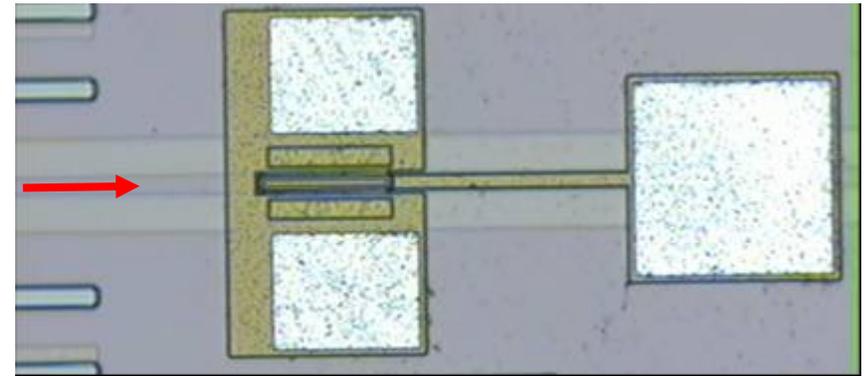
SEM Cross-Section



# World's best Waveguide Photodetector Performance

**Performance** combines

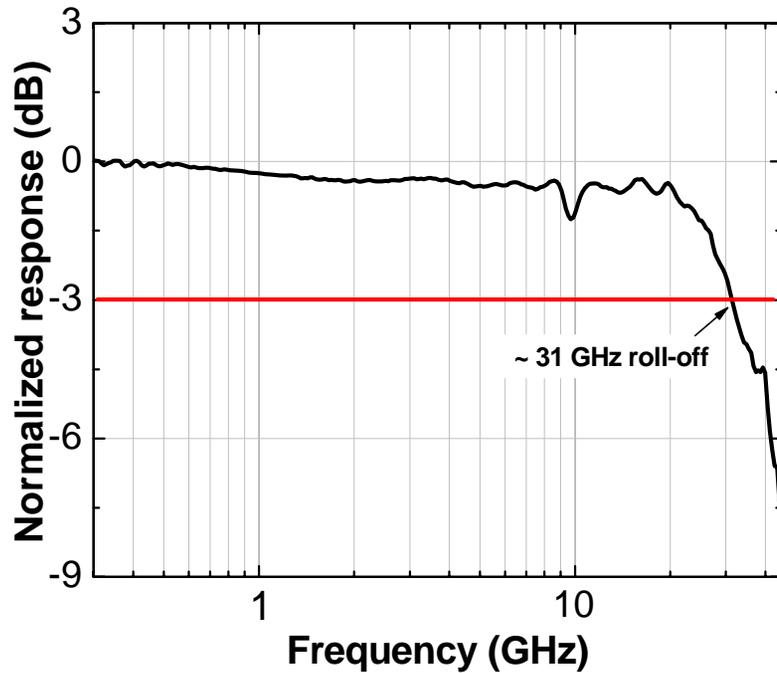
- **Speed**  
= bits per second
- **Efficiency**  
= % of photons detected
- **Noise**  
= "dark current")



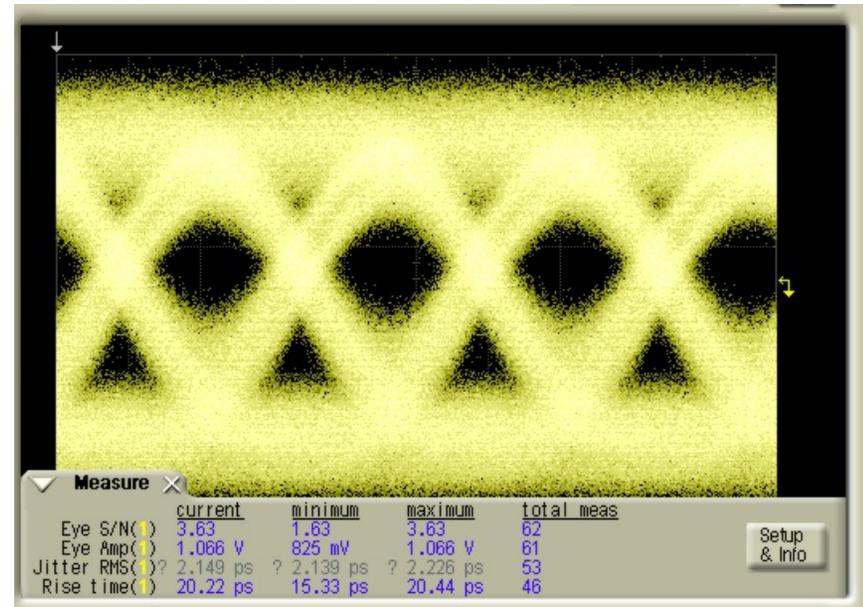
## Results:

- 40 Gb/s operation
- 95% efficient (up to  $\lambda \sim 1.56\mu\text{m}$ )
- < 200nA of dark current

# Experimental Results:



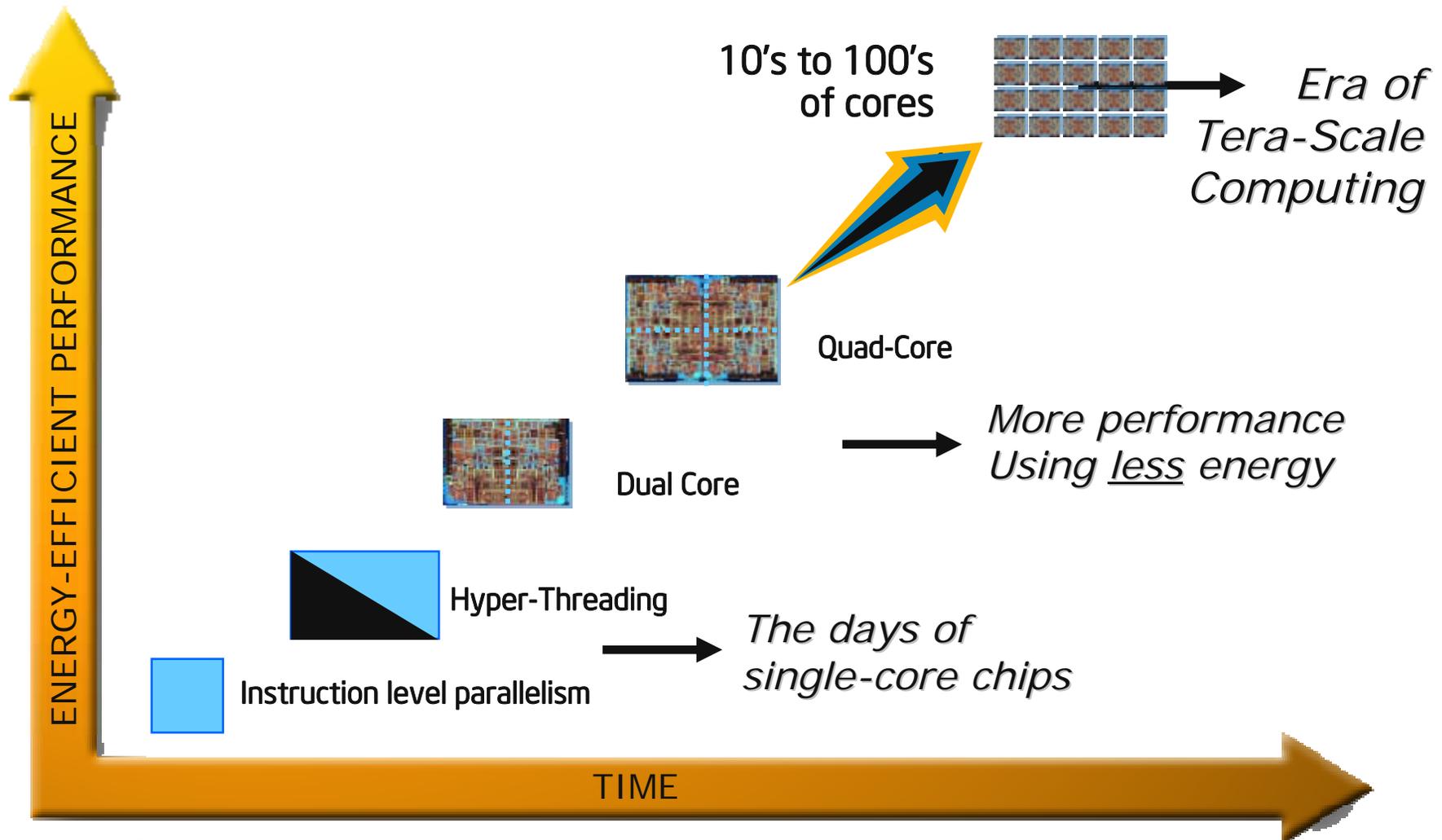
31 GHz Optical Bandwidth



40 Gb/s Data transmission

World's Best Performing Ge  
Waveguide Photodetector

# Tera-leap to Parallelism:



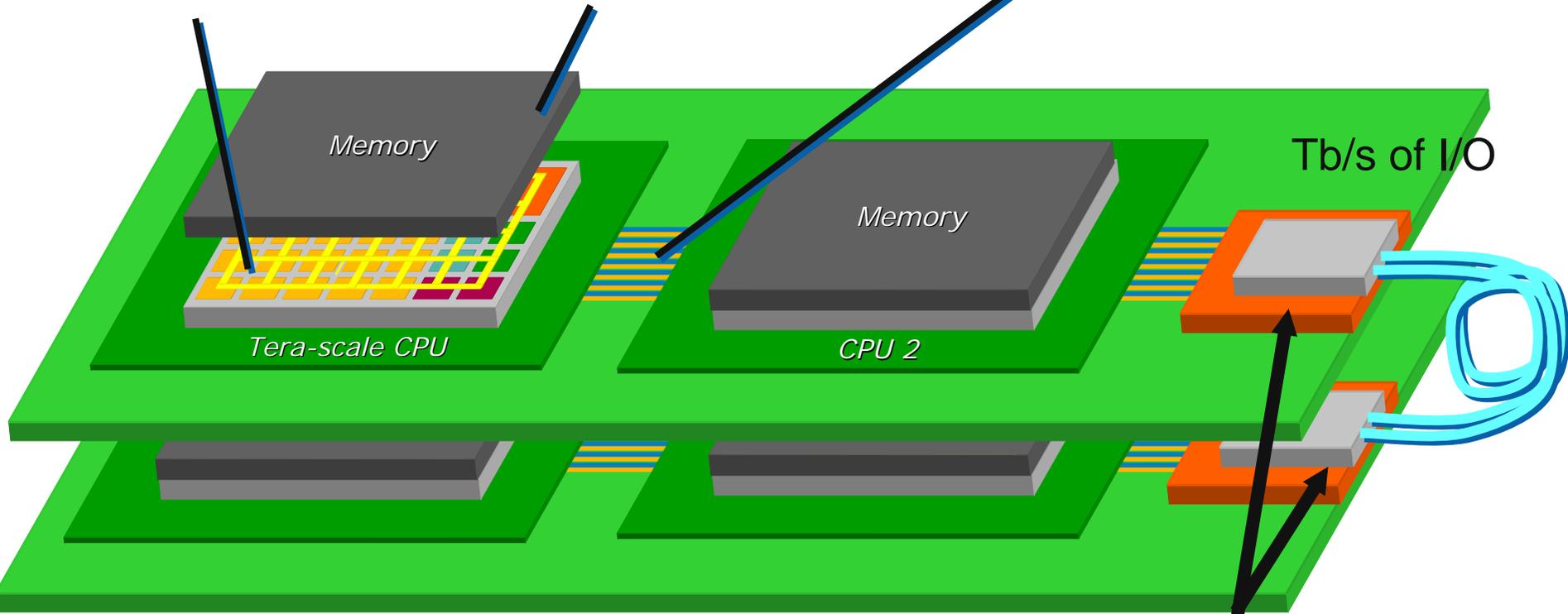
All this compute capability may require high speed optical links

# Future Physical I/O for a Tera-scale Servers

**Core-Core: On Die**  
Interconnect fabric

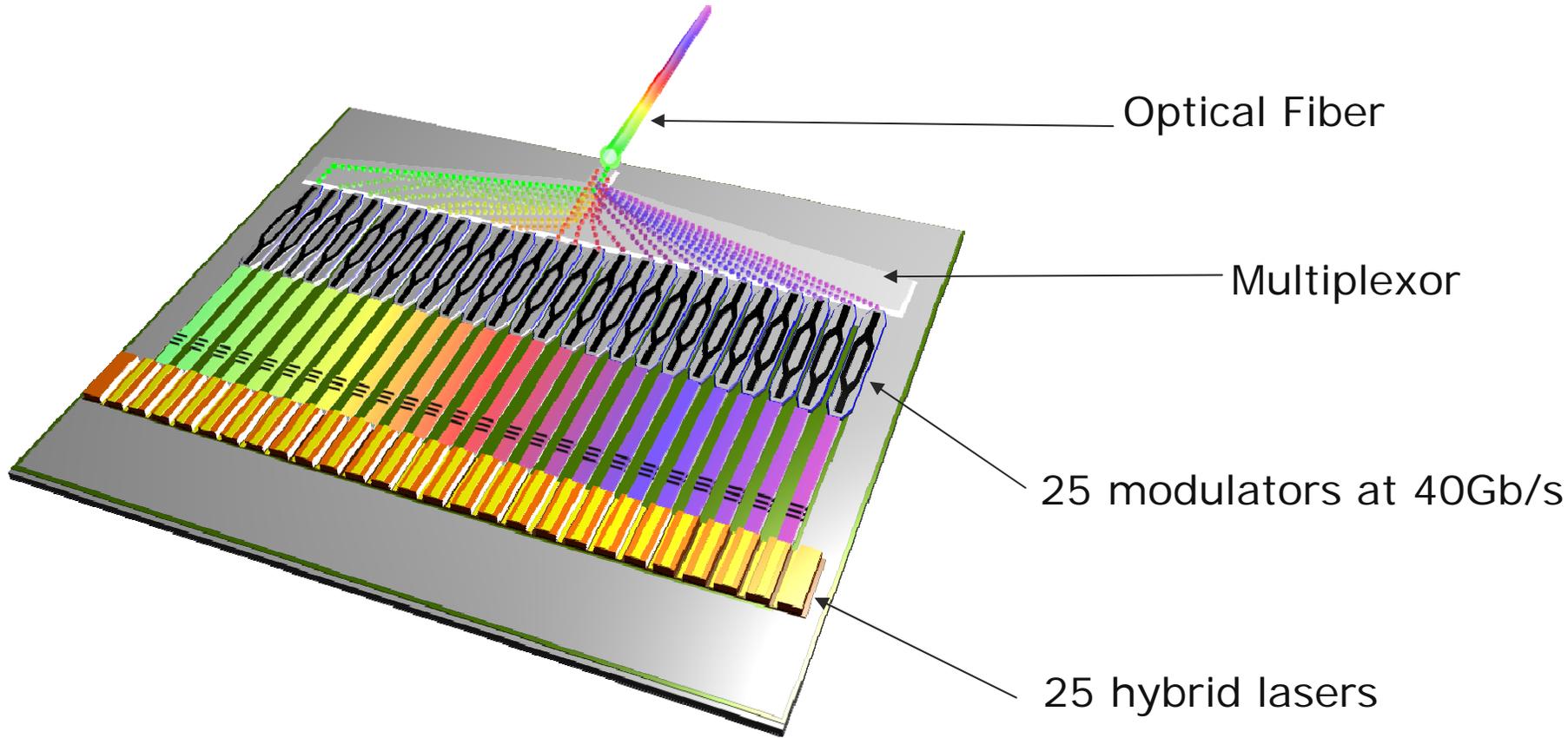
**Memory: Package**  
3D Stacking

**Chip-Chip: Fast Copper**  
FR4 or Flex cables



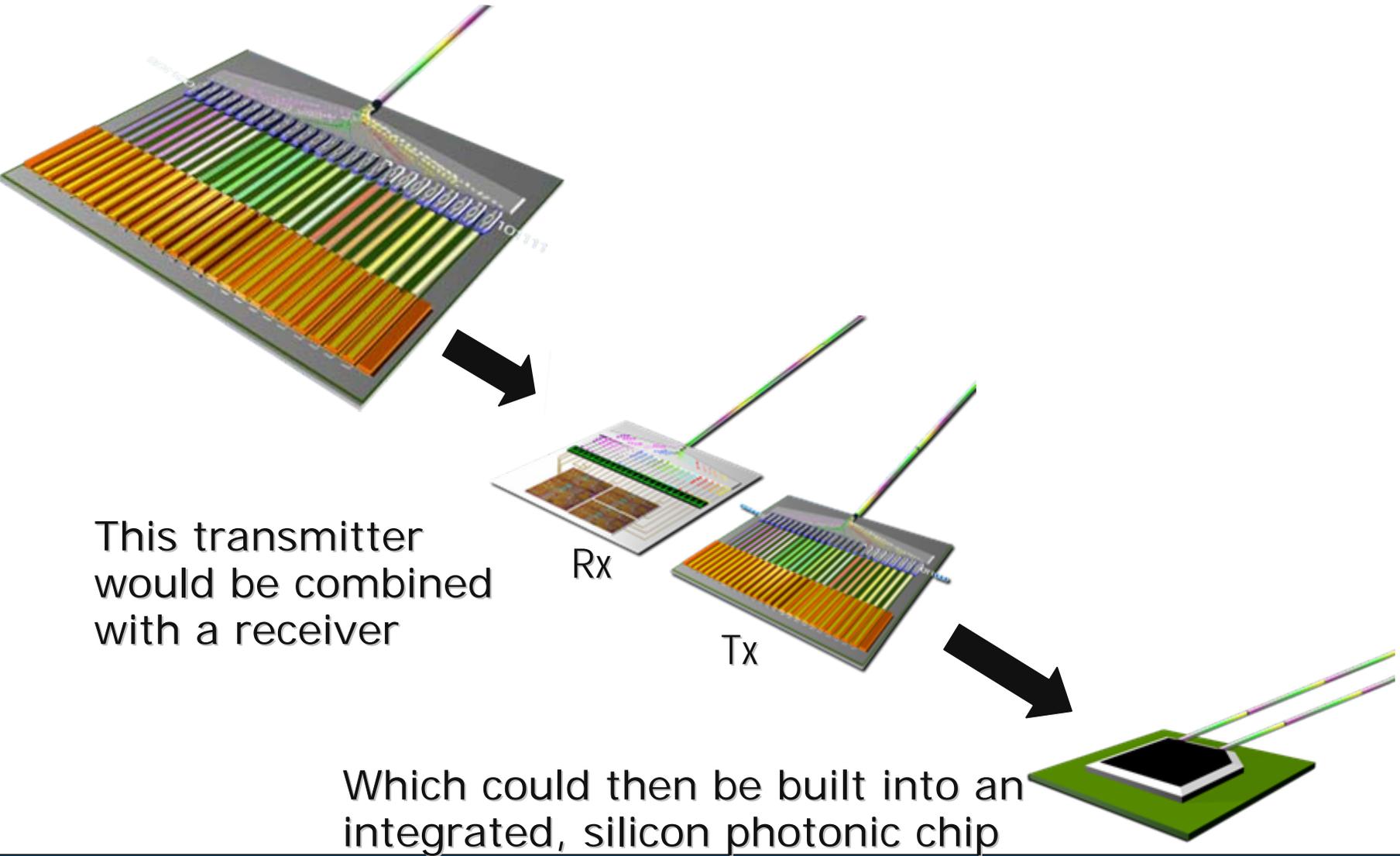
**Integrated Tb/s Optical Chip**

# Future: A Terabit Optical Chip

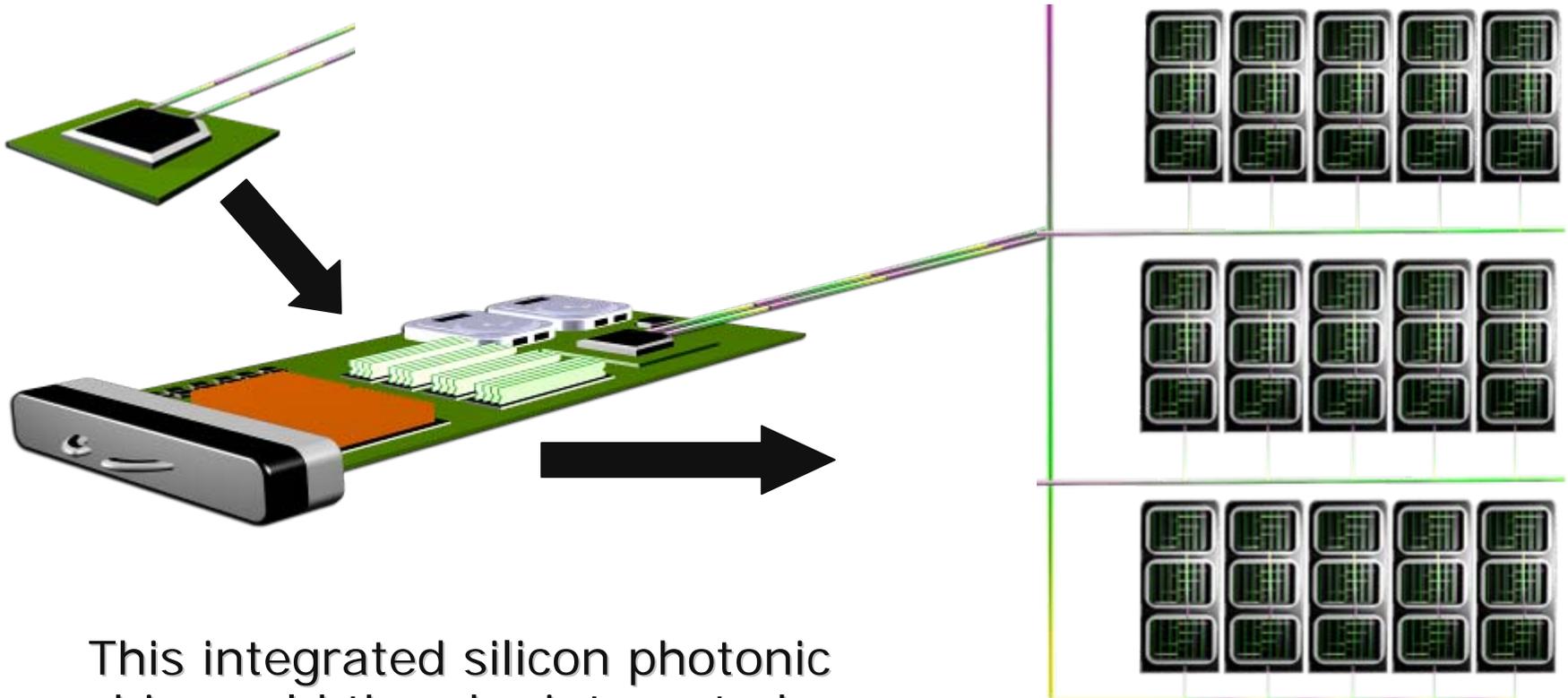


**A future integrated terabit per second optical link on a single chip**

# Integrating into a Tera-scale System



# Integrating into a Tera-scale System



This integrated silicon photonic chip could then be integrated into computer boards

And this board could be integrated into a Tera-scale system

Integration of photonic devices will be critical in future applications.

# Summary

## Worlds Best performing Silicon Germanium Photo-detector

- Capable of operating at 40 Gbps
- Low dark current and great responsivity
- Details to be presented at Group IV conference Tokyo Japan Sept 20<sup>th</sup>

## Background

- Silicon is transparent to Infrared light and good for routing light
- Germanium must be added to allow Silicon to absorb light
- Intel used a unique process to grow Germanium on Silicon and produce an efficient Silicon Germanium photo-detector

## Vision

- Build highly integrated Si Photonics chips for optical communication
- Build using high-volume, low cost manufacturing processes
- Enables terabit optical links

# Links

- Silicon Photonics at Intel site - <http://techresearch.intel.com/articles/Tera-Scale/1419.htm>
- Blog about recent modulator advance - [http://blogs.intel.com/research/2007/07/40g\\_modulator.html](http://blogs.intel.com/research/2007/07/40g_modulator.html)

# What We are Announcing

## Worlds Best performing Silicon Germanium Photodetector

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## Background

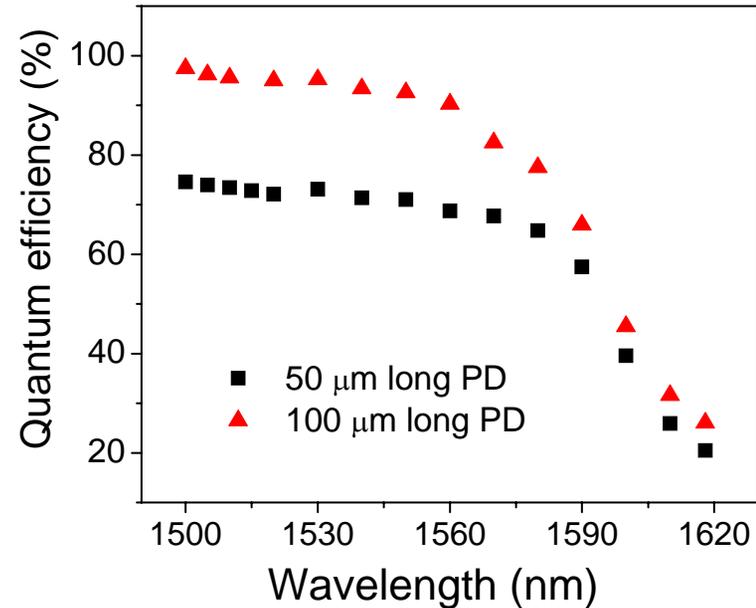
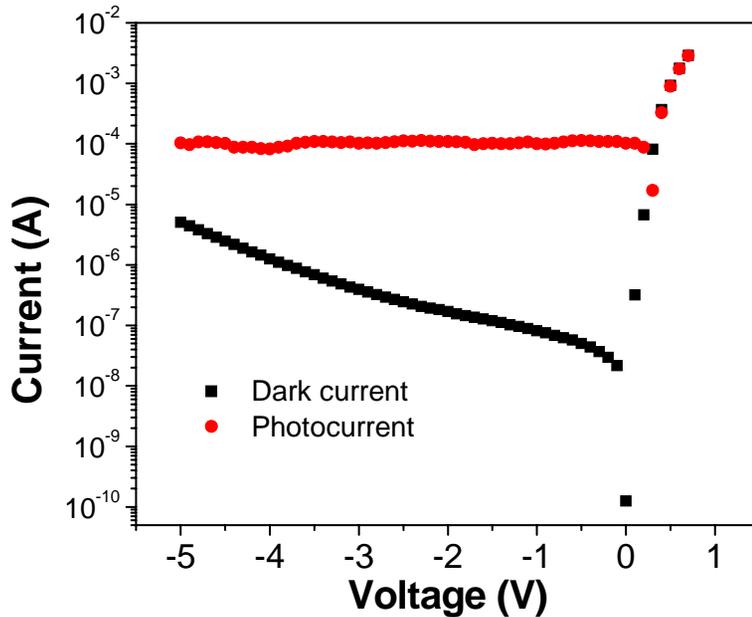
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## Vision

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- Build using high-volume, low cost manufacturing processes
- Enables terabit optical links for tera scale platforms



# DC Photodetector Performance



- Dark current of photodetector is still below noise floor of amplification circuitry.
- Quantum efficiency is excellent at ~95%.